



ALPHA & OMEGA
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AOS Semiconductor Product Reliability Report

AO6800, rev C

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

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THIS AOS product reliability report summarizes the qualification result for AO6800. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO6800 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

Table of Contents:

- I. Product Description
- II. Package and Die information
- III. Environmental Stress Test Summary and Result
- IV. Reliability Evaluation

I. Product Description:

The AO6800 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

- RoHS Compliant
- Halogen Free

Detailed information refers to datasheet.

II. Die / Package Information:

| | AO6800 |
|---------------------------------------|--|
| Process | Standard sub-micron 30V Dual N-channel MOSFET |
| Package Type | TSOP6 |
| Lead Frame | Cu |
| Die Attach | Ag Epoxy |
| Bonding Wire | Au wire |
| Mold Material | Epoxy resin with silica filler |
| MSL (moisture sensitive level) | Level 1 based on J-STD-020 |

Note * based on information provided by assembler and mold compound supplier

III. Result of Reliability Stress for AO6800

| Test Item | Test Condition | Time Point | Lot Attribution | Total Sample size | Number of Failures | Standard |
|-------------------|---|-------------------------------|-------------------------------|------------------------------|--------------------|-------------|
| MSL Precondition | 168hr 85°C /85%RH +3 cycle reflow@260°C | - | 27 lots | 4917 pcs | 0 | JESD22-A113 |
| HTGB | Temp = 150 °c, Vgs=100% of Vgsmax | 168hrs 500 hrs 1000 hrs | 6 lots 5 lots (Note A*) | 847pcs 77pcs / lot | 0 | JESD22-A108 |
| HTRB | Temp = 150 °c, Vds=80% of Vdsmax | 168hrs 500 hrs 1000 hrs | 6 lots 5 lots (Note A*) | 847pcs 77pcs / lot | 0 | JESD22-A108 |
| HAST | 130 +/- 2°C, 85%RH, 33.3 psi, Vgs = 100% of Vgs max | 100 hrs | 18 lots (Note A*) | 990 pcs 55 pcs / lot | 0 | JESD22-A110 |
| Pressure Pot | 121°C, 29.7psi, RH=100% | 96 hrs | 24 lots (Note A*) | 1848 pcs 77 pcs / lot | 0 | JESD22-A102 |
| Temperature Cycle | -65°C to 150°C, air to air | 250 / 500 cycles | 27 lots (Note A*) | 2079 pcs 77 pcs / lot | 0 | JESD22-A104 |

Note A: The reliability data presents total of available generic data up to the published date.

IV. Reliability Evaluation

FIT rate (per billion): 3
MTTF = 39656 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO6800). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)]$$

$$= 1.83 \times 10^9 / [2x (12x77x168 + 6x77x500 + 4x77x1000) x258] = 3$$

$$\text{MTTF} = 10^9 / \text{FIT} = 3.47 \times 10^8 \text{hrs} = 39656 \text{ years}$$

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [Af] = **Exp** ^[Ea / k (1/Tj u - 1/Tj s)]

Acceleration Factor ratio list:

| | 55 deg C | 70 deg C | 85 deg C | 100 deg C | 115 deg C | 130 deg C | 150 deg C |
|----|----------|----------|----------|-----------|-----------|-----------|-----------|
| Af | 258 | 87 | 32 | 13 | 5.64 | 2.59 | 1 |

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

K = Boltzmann's constant, 8.617164 X 10⁻⁵eV / K